

2SK1299(L), 2SK1299(S)

Silicon N-Channel MOS FET

Application

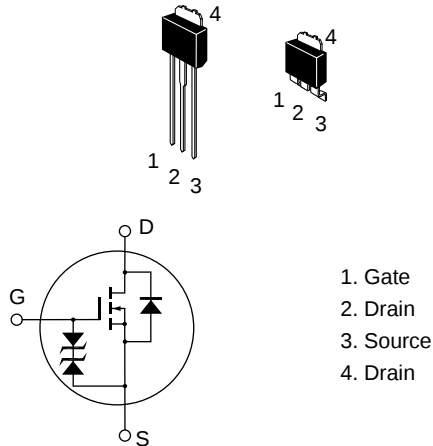
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline

DPAK-1



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	3	A
Drain peak current	I _{D(pulse)} ^{*1}	12	A
Body to drain diode reverse drain current	I _{DR}	3	A
Channel dissipation	Pch ^{*2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at T_c = 25°C

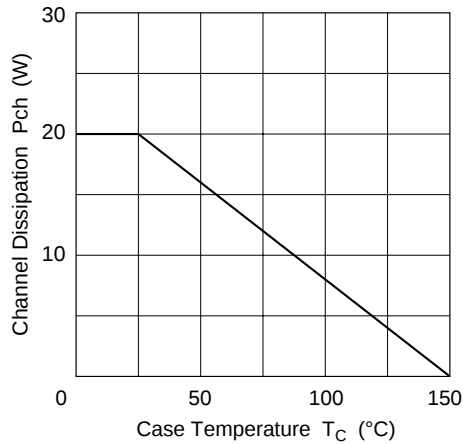
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10\text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	100	μA	$V_{DS} = 80\text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1\text{ mA}$, $V_{DS} = 10\text{ V}$
Static Drain to source on state resistance	$R_{DS(on)}$	—	0.25	0.35	Ω	$I_D = 2\text{ A}$, $V_{GS} = 10\text{ V}^{*1}$
		—	0.30	0.45	Ω	$I_D = 2\text{ A}$, $V_{GS} = 4\text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	2.4	4.0	—	S	$I_D = 2\text{ A}$, $V_{DS} = 10\text{ V}^{*1}$
Input capacitance	C_{iss}	—	400	—	pF	$V_{DS} = 10\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$
Output capacitance	C_{oss}	—	165	—	pF	
Reverse transfer capacitance	C_{rss}	—	45	—	pF	
Turn-on delay time	$t_{d(on)}$	—	5	—	ns	$I_D = 2\text{ A}$, $V_{GS} = 10\text{ V}$, $R_L = 15\text{ }\Omega$
Rise time	t_r	—	35	—	ns	
Turn-off delay time	$t_{d(off)}$	—	160	—	ns	
Fall time	t_f	—	60	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 3\text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	135	—	ns	$I_F = 3\text{ A}$, $V_{GS} = 0$, $di_F/dt = 50\text{ A}/\mu\text{s}$

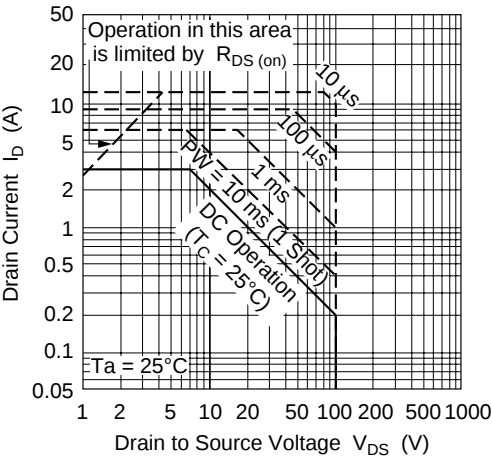
Note: 1. Pulse test

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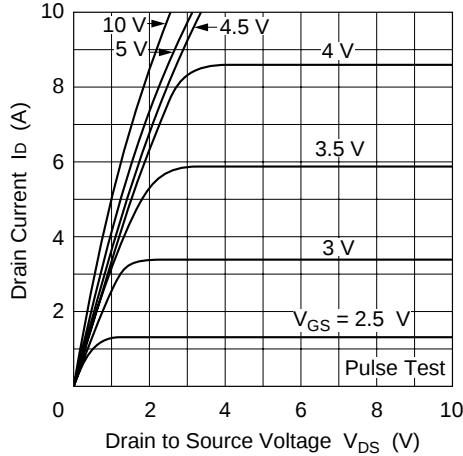
Power vs. Temperature Derating



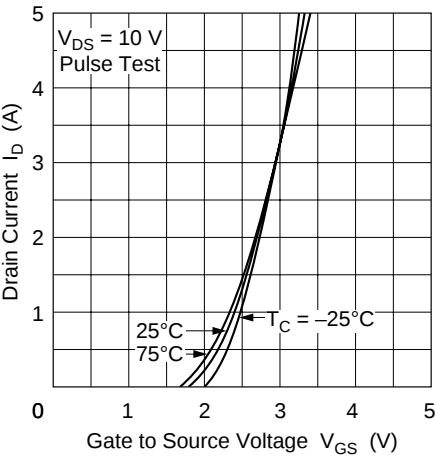
Maximum Safe Operation Area

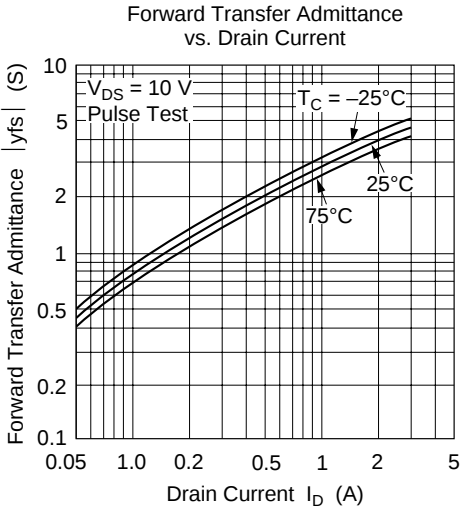
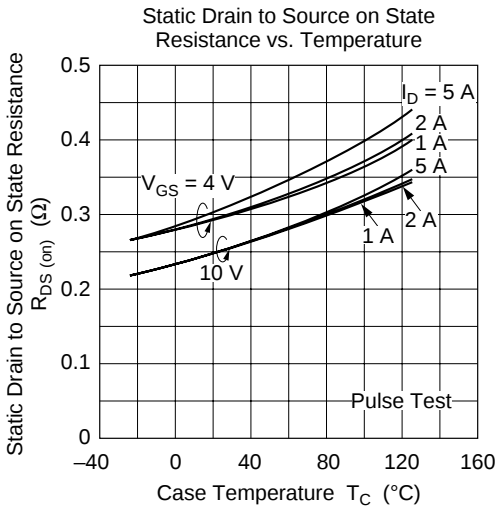
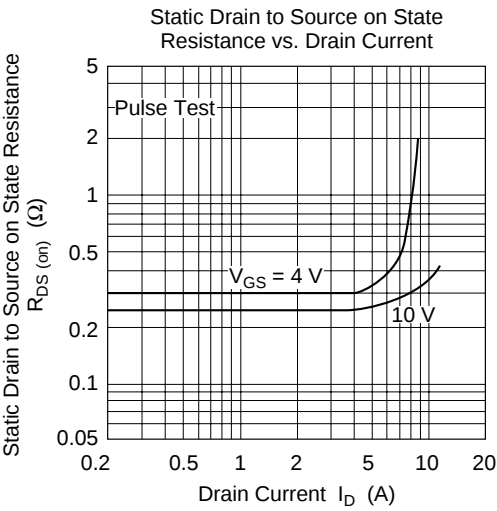
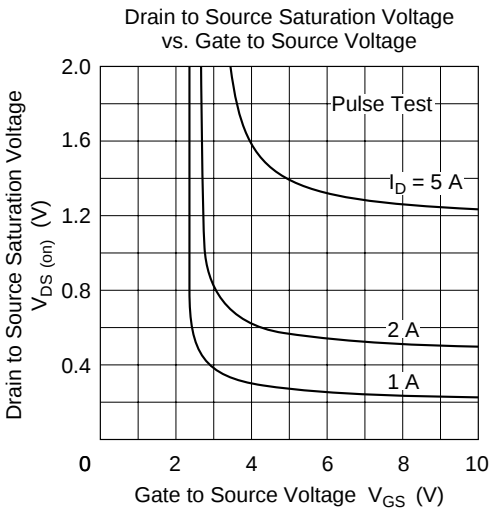


Typical Output Characteristics



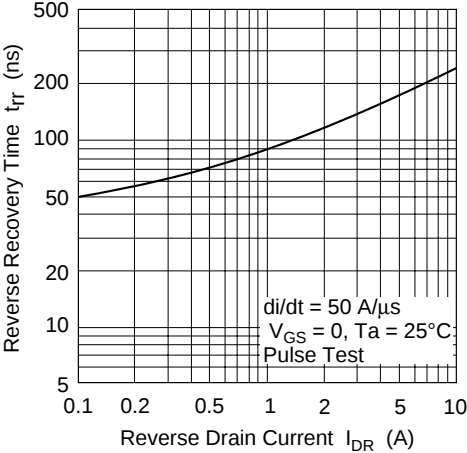
Typical Transfer Characteristics



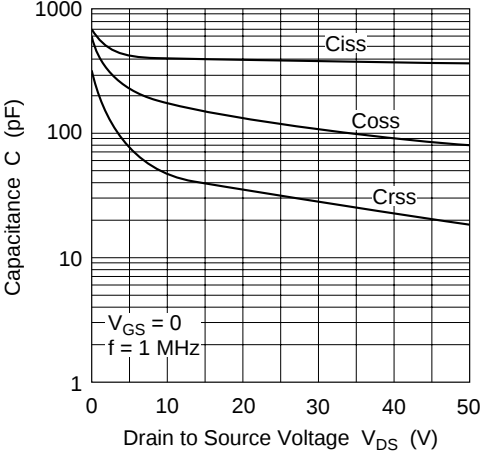


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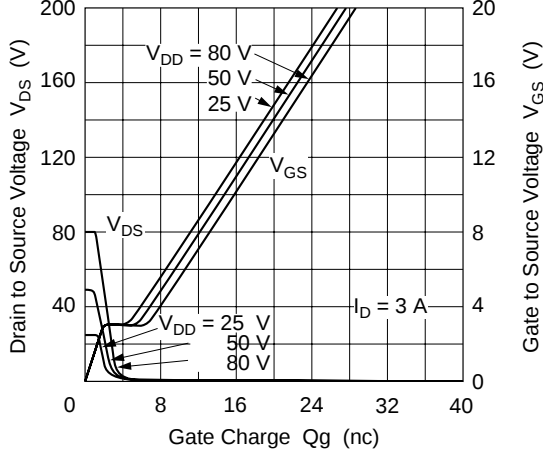
Body to Drain Diode Reverse Recovery Time



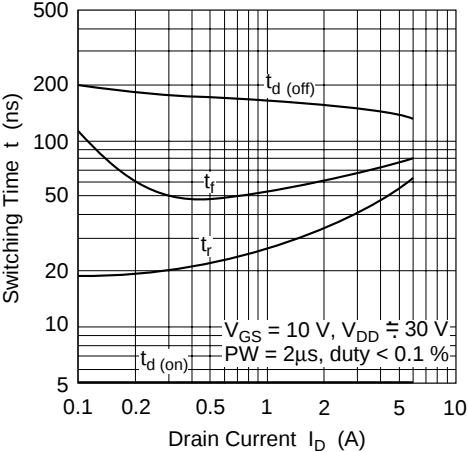
Typical Capacitance vs. Drain to Source Voltage

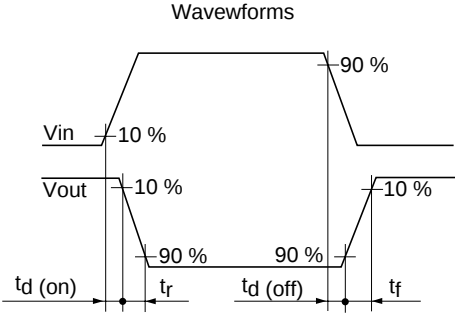
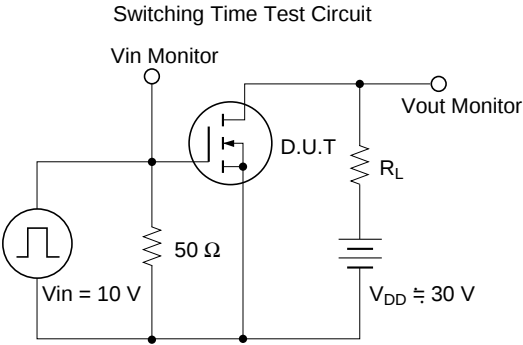
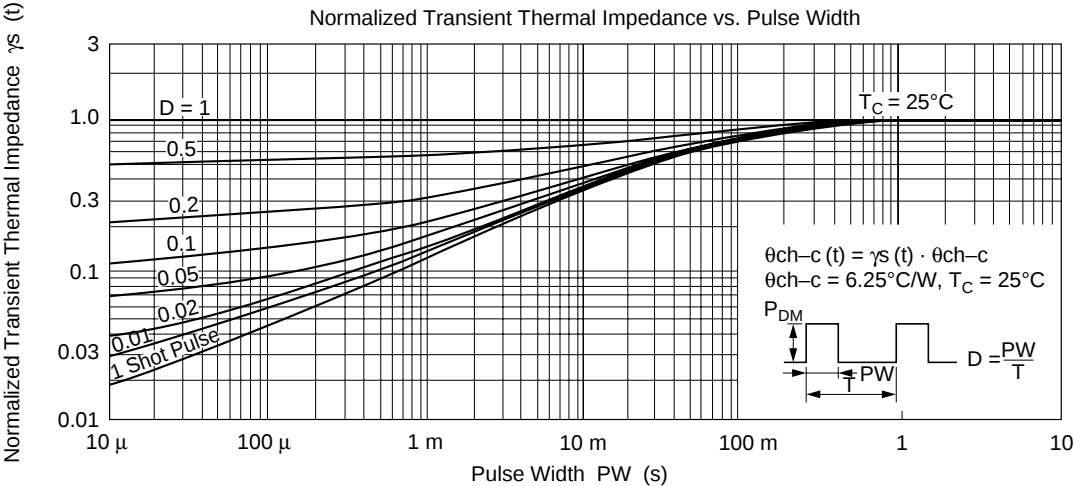
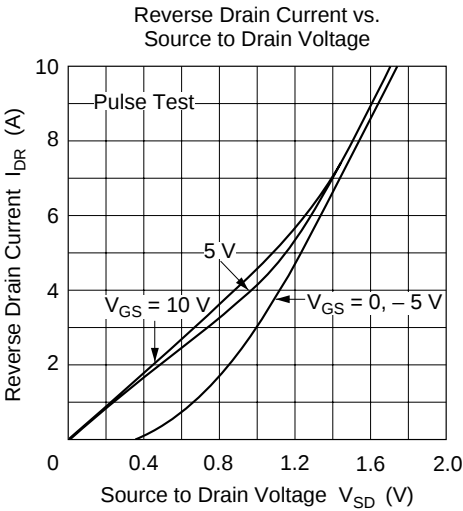


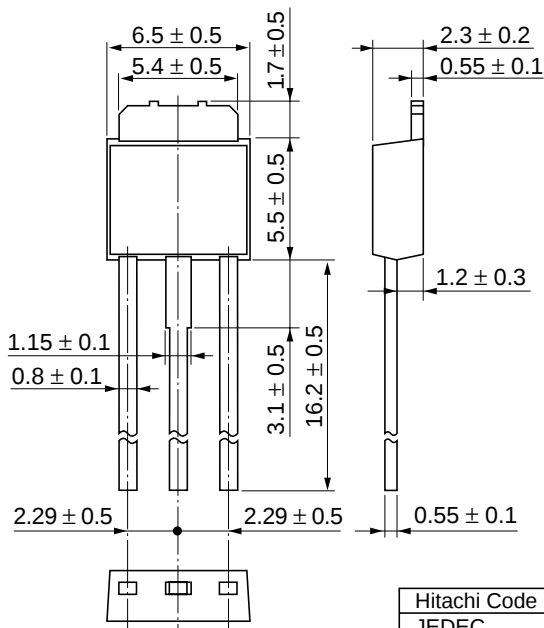
Dynamic Input Characteristics



Switching Characteristics







Hitachi Code	DPAK (L)-(1)
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.42 g